

N-Ch 100V Fast Switching MOSFET VDs=100V, ID=4.0A, RDS(ON)=100mΩ

General Description

This PAN26TB02QB N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent Rds(On) performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

Feature

- •Green Device Available
- •Super Low Gate Charge
- •Excellent CdV/dt effect decline
- Advanced high cell density Trench technology
- ●SOT-223 package design

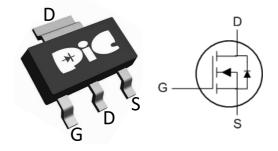
> <u>Application</u>

- Motor and Load Control
- Power Management in White LED System
- Push Pull Converter
- ●LCD TV Inverter & AD/DC Inverter Systems.

Absolute Maximum Ratings

Parameter		Symbol	Maximum Ratings	Unit	
Drain-Source Voltage		Vds	100	V	
Gate-Source Voltage		Vgs	±20	V	
Continuous Drain Current	TA=25 ℃	lo	4	А	
	T a=70 ℃		3.2		
Pulsed Drain Current		Ідм	16	А	
Mauinauna Dauran Diagingtian	TA=25 ℃	PD	3	10/	
Maximum Power Dissipation	T a=70 ℃		1.9	W	
Operating Junction Temperature		TJ	150	°C	
Storage Temperature Range		Tstg	-55 to 150	°C	
Thermal Resistance-Junction to Ambient		Reja	42	°C/W	

SOT-223





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Electrical Characteristics (TJ=25°C Unless otherwise noted)

Symbol	Parameter	Limit	Min	Тур	Мах	Unit	
STATIC				•			
VBR(DSS)	Drain-Source Breakdown Voltage	Vgs=0V, ID=250 μ A	100			V	
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250 μ A	1.0		3.0	V	
lgss	Gate Leakage Current	VDS=0V, VGS=±20V			±100	nA	
ldss	Zero Gate Voltage Drain Current	VDS=100V, VGS=0V			1	μ Α	
Rds(ON)	Drain-Source On-Resistance ^a	Vgs=10V, Id= 3.7A		80	100	- m Ω	
		Vgs=4.5V, ID= 3.5A		85	115		
Vsd	Diode Forward Voltage	Is=2.5A, Vgs=0V		0.8	1.2	V	
DYNAMIC						•	
Qg	Total Gate Charge	VDS=80V, VGS=10V, ID=2.5A		24		nC	
Qg	Total Gate Charge			14			
Qgs	Gate-Source Charge	VDS=80V, VGS=4.5V, ID=2.5A		3.8			
Qgd	Gate-Drain Charge			7.5			
Ciss	Input capacitance			905			
Coss	Output Capacitance	VDs=15V, VGs=0V, f=1.0MHz		145		pF	
Crss	Reverse Transfer Capacitance			43			
Rg	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz		1		Ω	
t d(on)	Turn-On Delay Time			15			
tr	Turn-On Rise Time	Vdd=50V, RL =10Ω		8			
td(off)	Turn-Off Delay Time	VGEN=10V, RG=6 Ω		47		ns	
tr	Turn-Off Fall Time			6			

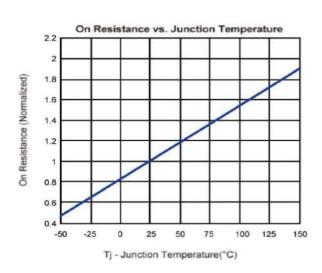
Notes: a. Pulse test: pulse width \leq 300us, duty cycle \leq 2%, Guaranteed by design, not subject to production testing.

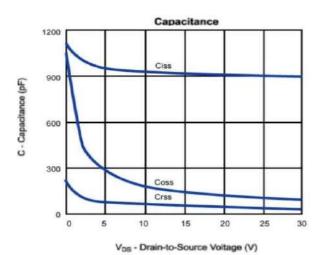


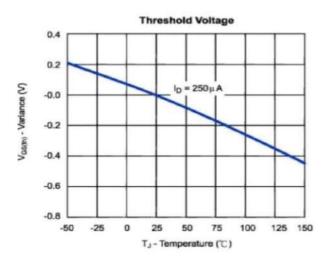
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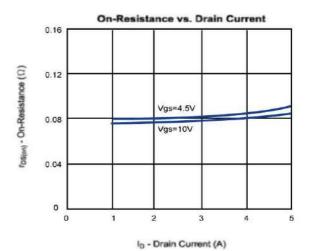
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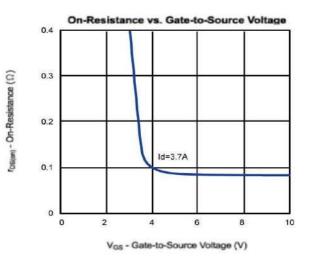


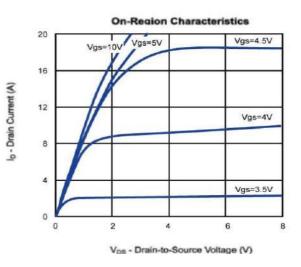








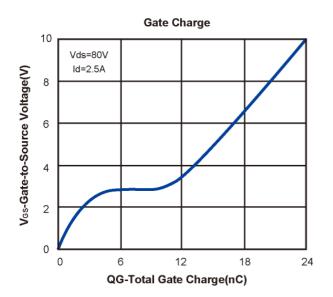




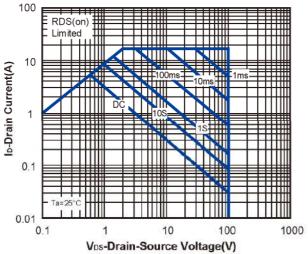
Spec No:35408A09 Date:2017.Jun Revision:D

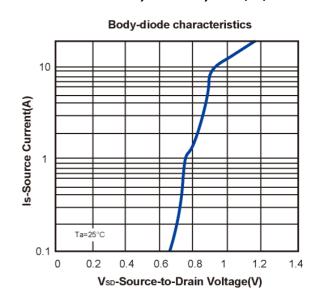


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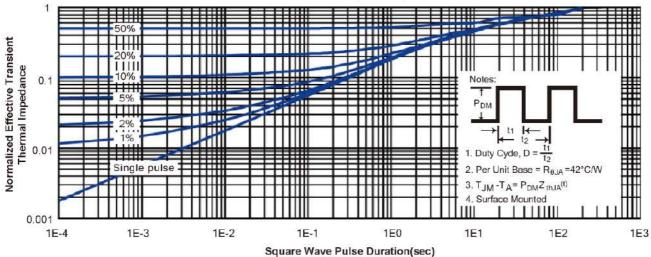








Normalized Thermal Transient Impedance, Junction-to-Ambient

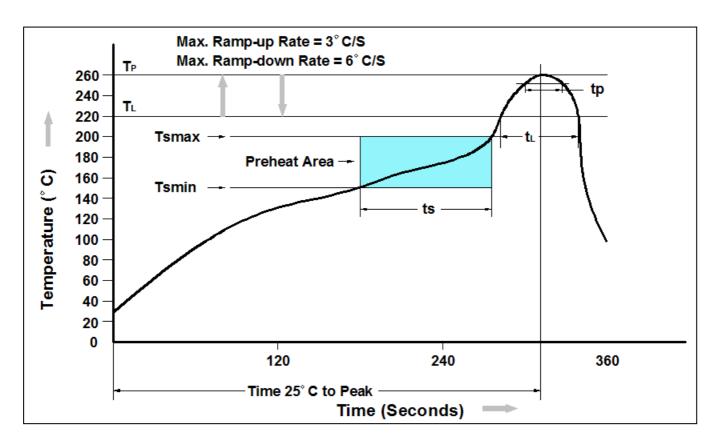




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<u>Recommand IR Reflow Soldering Thermal Profile</u>



Profile Feature	Pb-Free Assembly Profile	
Temperature Min. (Tsmin)	150°C	
Temperature Max. (Tsmax)	200°C	
Time (ts) from (Tsmin to Tsmax)	60-120 seconds	
Average Ramp-up Rate (tL to tP)	3°C/second max.	
Liquidous Temperature (TL)	217°C	
Time (tL) Maintained Above (TL)	60 – 150 seconds	
Peak Temperature	260°C +0°C /-5°C	
ne (tP) within 5°C of actual Peak Temperature 30 seconds		
Ramp-down Rate (TP to TL)	6°C/second max	
Time 25°C to Peak Temperature	8 minutes max.	

Ordering Information

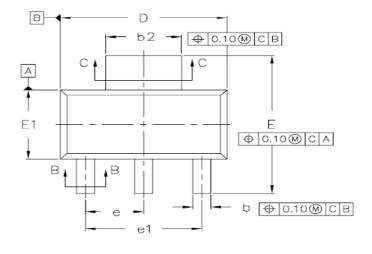
Part Number	Description	Quantity
PAN26TB02QB	SOT-223 Reel	3000 pcs

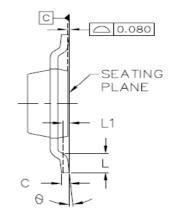


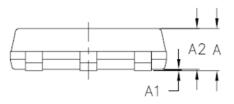
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Package Information (SOT-223)







Ş	COMMON				
MBO .	MM		INCH		
L S	MIN.	MAX.	MIN.	MAX.	
A		1.80		0.071	
A1	0.02	0.10	0.001	0.004	
A2	1.50	1.70	0.059	0.067	
b	0.66	0.84	0.026	0.033	
b1	0.60	0.79	0.024	0.031	
b2	2.90	3.10	0.114	0.122	
b3	2.84	3.05	0.112	0.120	
с	0.23	0.35	0.009	0.014	
c1	0.23	0.33	0.009	0.013	
D	6.30	6.70	0.248	0.264	
E	6.70	7.30	0.264	0.287	
E1	3.30	3.70	0.130	0.146	
e	2.30 BSC.		0.091 BSC.		
e1	4.60 BSC.		0.182 BSC.		
L	0.81		0.032		
L1	0.25	0.25 BSC.		BSC.	
0	0.	10*	0.	10*	



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